

Silicon NPN Power Transistors

2SC5802

DESCRIPTION

- With TO-3P(H)IS package
- High voltage;high speed
- Wide area of safe operation

APPLICATIONS

- For high voltage color display horizontal deflection output applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

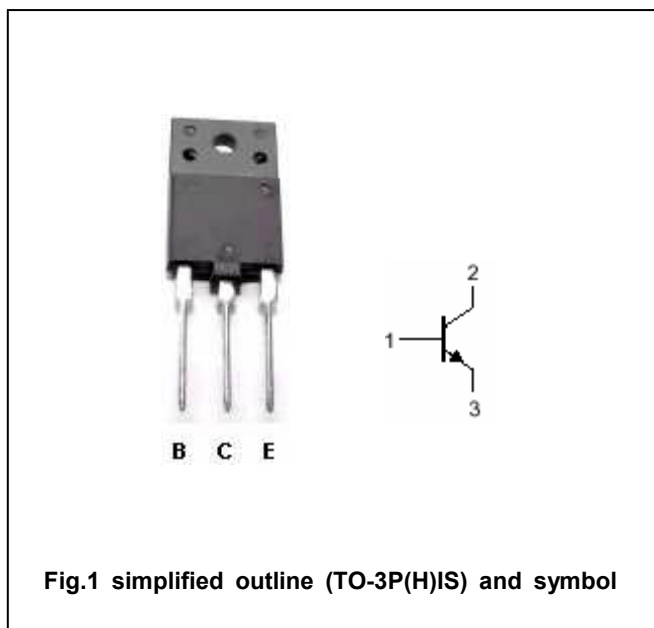


Fig.1 simplified outline (TO-3P(H)IS) and symbol

Absolute maximum ratings($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1500	V
V_{CEO}	Collector-emitter voltage	Open base	800	V
V_{EBO}	Emitter-base voltage	Open collector	6	V
I_C	Collector current		10	A
I_{CM}	Collector current-Peak		30	A
P_C	Total power dissipation	$T_C=25^\circ\text{C}$	60	W
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-55~150	$^\circ\text{C}$

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEsat}	Collector-emitter saturation voltage	I _C =6A; I _B =1.5A			3.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =6A; I _B =1.5A			1.5	V
I _{CES}	Collector cut-off current	V _{CE} =1400V; V _{BE} =0			1.0	mA
I _{CBO}	Collector cut-off current	V _{CB} =800V; I _E =0			10	μA
I _{EBO}	Emitter cut-off current	V _{EB} =4V; I _C =0			1.0	mA
h _{FE-1}	DC current gain	I _C =1A; V _{CE} =5V	15		48	
h _{FE-2}	DC current gain	I _C =6A; V _{CE} =5V	7		10	
t _f	Fall time	V _{CC} =200V; I _C =6A; I _{B1} =1.2A I _{B2} =-2.4A; R _L =33.3Ω		0.1	0.3	μs

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PACKAGE OUTLINE

